

OT406 Four-quadrant triac, enhanced noise immunity Rev. 01 — 19 May 2008 P

Product data sheet

Product profile

1.1 General description

Passivated sensitive gate triac in a SOT223 surface-mountable plastic package

1.2 Features

- Sensitive gate
- Direct interfacing to logic level ICs
- Enhanced immunity to voltage transients and noise
- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits
- Blocking voltage to 600 V

1.3 Applications

- Home appliances
- Low power AC fan speed controllers
- Low power motor control
- Low power loads in industrial process control

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V}$
- $I_{TSM} \le 12.5 \text{ A (t = 20 ms)}$
- $I_{T(RMS)} \le 1 A$

- $I_{GT} \le 3 \text{ mA}$
- $I_{GT} \le 5 \text{ mA } (T2-G+)$

Pinning information

Table 1. **Pinning**

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------------------------------|--------------------|----------------|
| 1 | main terminal 1 (T1) | | N 1 |
| 2 | main terminal 2 (T2) | 4 | T2—T1 |
| 3 | gate (G) | | sym051 |
| 4 | mounting base; main terminal 2 (T2) | 1 2 3 | |
| | | SOT223 | |



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3. Ordering information

Table 2. Ordering information

| Type number | Package | | | |
|-------------|---------|--|---------|--|
| | Name | Description | Version | |
| OT406 | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 | |

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|---|-----|------|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 600 | V |
| V_{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{sp} \le 103$ °C; see Figure 4 and 5 | - | 1 | Α |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3 | | | |
| | | t = 20 ms | - | 12.5 | Α |
| | | t = 16.7 ms | - | 13.8 | Α |
| l ² t | I ² t for fusing | t _p = 10 ms | - | 1.28 | A ² s |
| dl _T /dt | rate of rise of on-state current | $I_{TM} = 1 \text{ A}; I_G = 20 \text{ mA};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$ | | | |
| | | T2+ G+ | - | 50 | A/μs |
| | | T2+ G- | - | 50 | A/μs |
| | | T2- G- | - | 50 | A/μs |
| | | T2- G+ | - | 10 | A/μs |
| I _{GM} | peak gate current | | - | 1 | Α |
| P_{GM} | peak gate power | | - | 2 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.1 | W |
| T _{stg} | storage temperature | | -40 | +150 | °C |
| T _j | junction temperature | | - | 125 | °C |

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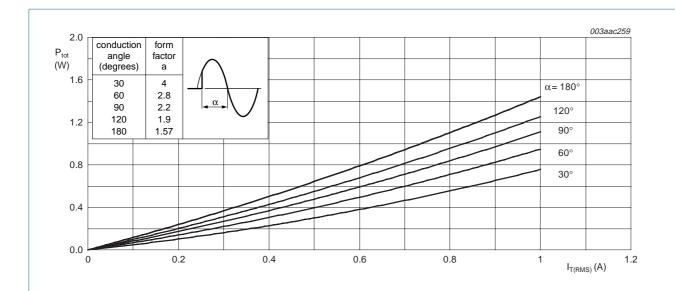


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

 α = conduction angle

f = 50 Hz

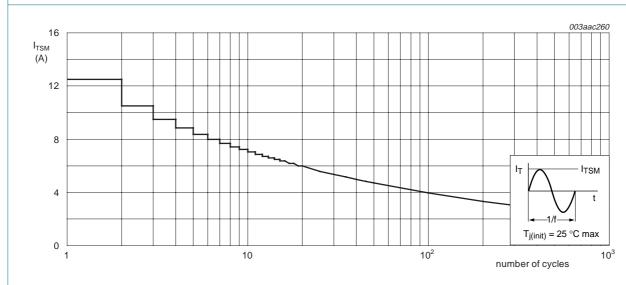
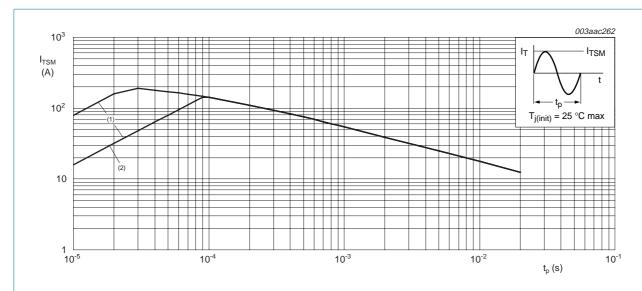


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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 $t_p \le 20 \text{ ms}$

- (1) dI_T/dt limit
- (2) T2- G+ quadrant limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values

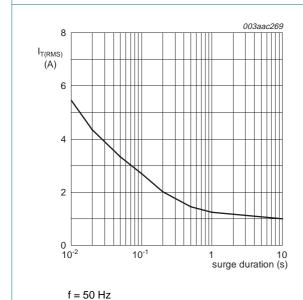


Fig 4. RMS on-state current as a function of surge duration; maximum values

 $T_{sp} = 103 \, ^{\circ}C$

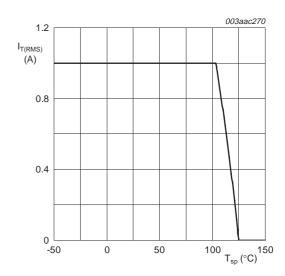


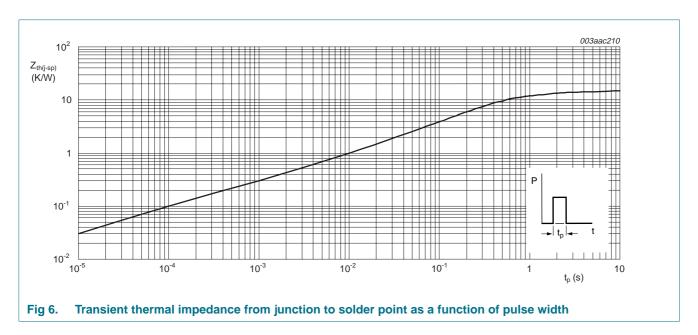
Fig 5. RMS on-state current as a function of solder point temperature; maximum values

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5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--------------------------------------|-----------------|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | full cycle; see Figure 6 | - | - | 15 | K/W |
| R _{th(j-a)} | | full cycle | | | | |
| | ambient | for minimum footprint see Figure 13 | otprint - 156 - | - | K/W | |
| | | for pad area see <u>Figure 14</u> | - | 70 | - | K/W |



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6. Static characteristics

Table 5. Static characteristics

 $T_j = 25 \,^{\circ}C$ unless otherwise specified.

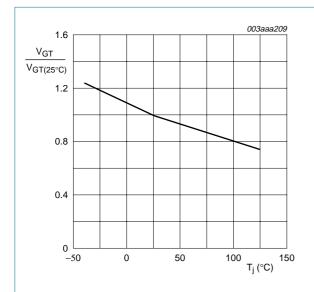
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------|----------------------|---|-----|-----|-----|------|
| I _{GT} | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 8}}{}$ | | | | |
| | | T2+ G+ | - | - | 3 | mA |
| | | T2+ G- | - | - | 3 | mA |
| | | T2- G- | - | - | 3 | mA |
| | | T2- G+ | - | - | 5 | mA |
| I _L latching current | latching current | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; see } \frac{\text{Figure 10}}{\text{ of } 100000000000000000000000000000000000$ | | | | |
| | | T2+ G+ | - | - | 7 | mA |
| | | T2+ G- | - | - | 20 | mA |
| | | T2- G- | - | - | 7 | mA |
| | | T2- G+ | - | - | 7 | mA |
| I _H | holding current | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; see } \frac{\text{Figure } 11}{}$ | - | - | 7 | mA |
| V_{T} | on-state voltage | I _T = 1 A; see <u>Figure 9</u> | - | 1.3 | 1.6 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 7}}{}$ | - | - | 1.3 | V |
| | | $V_D = V_{DRM}; I_T = 0.1 A; T_j = 125 ^{\circ}C$ | 0.2 | - | - | V |
| I _D | off-state current | $V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$ | - | - | 0.5 | mA |
| | | b branchady j | | | | |

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7. Dynamic characteristics

Table 6. Dynamic characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--|-----|-----|-----|------|
| dV _D /dt | rate of rise of off-state voltage | $V_{DM} = 0.67 V_{DRM(max)}$; $T_j = 110 ^{\circ}\text{C}$; exponential waveform; gate open circuit | 10 | - | - | V/μs |
| dV _{com} /dt | rate of change of commutating voltage | $V_{DM} = 400 \text{ V}; T_j = 110 ^{\circ}\text{C}; I_{TM} = 1 \text{ A}; \\ dI_{com}/dt = 0.44 \text{ A/ms}$ | 0.5 | - | - | V/μs |



1 003aaa205

1GT (25°C)

3 (1)
(2)
(3)
(4)

1 0

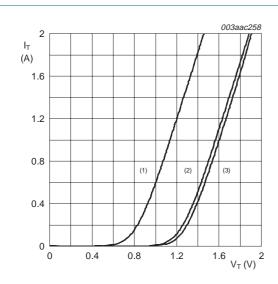
-50 0 50 100 T_j (°C)

- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2-G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

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 $V_0 = 1.254 \text{ V}; R_s = 0.31 \Omega$

- (1) $T_i = 125 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 125 \,^{\circ}C$; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 9. On-state current as a function of on-state voltage

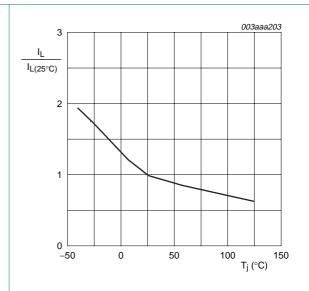


Fig 10. Normalized latching current as a function of junction temperature

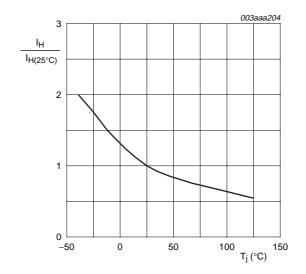


Fig 11. Normalized holding current as a function of junction temperature

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8. Package outline

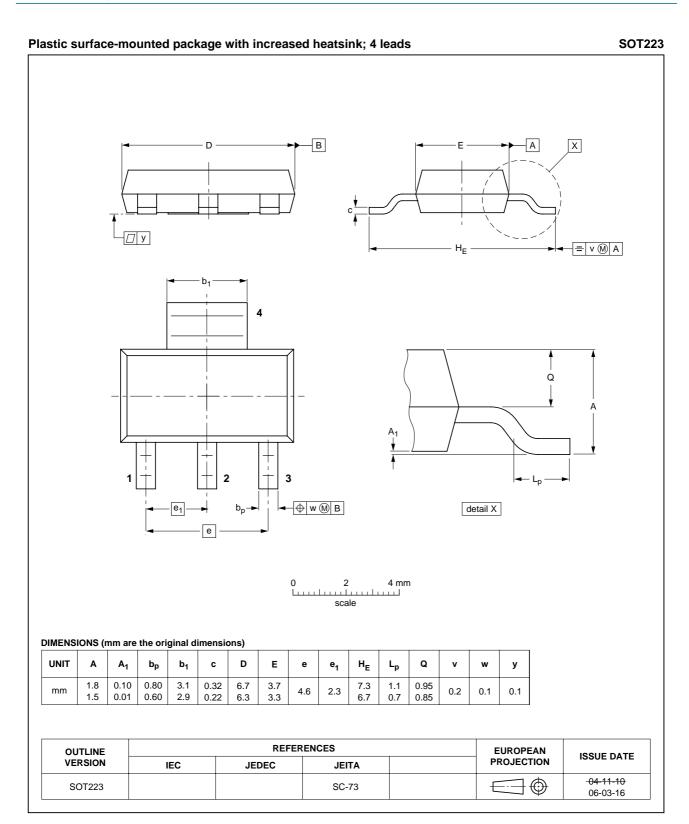


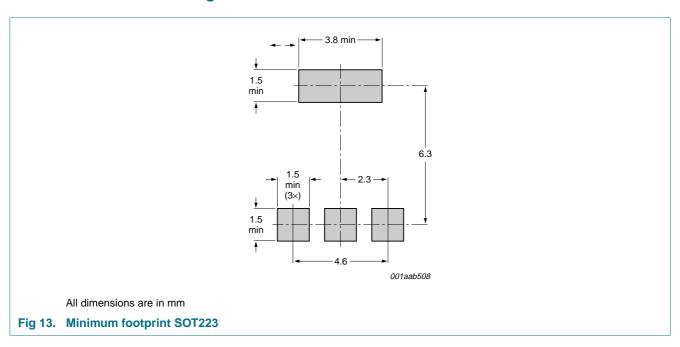
Fig 12. Package outline SOT223 (SC-73)

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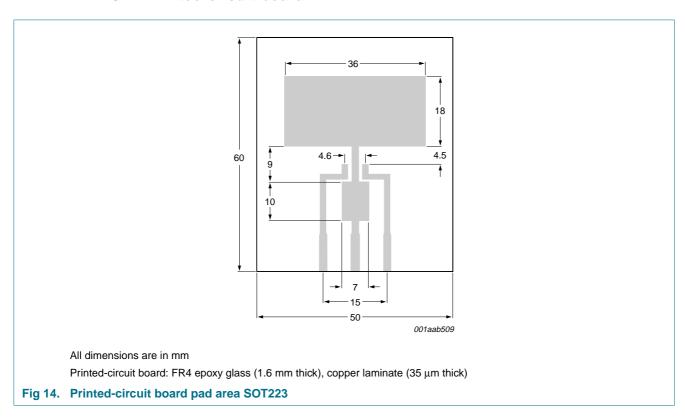
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9. Mounting

9.1 Mounting instructions



9.2 Printed-circuit board



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10. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| OT406_1 | 20080519 | Product data sheet | - | - |

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| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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Date of release: 19 May 2008
Document identifier: OT406_1

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